# 3DD505,BU104

## NPN Silicon Low Frequency High Power Transistor

**Features:**

1. Heavy working current.Good temperature stability.Excellent thermal fatigue capability.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch,low frequency power amplify,power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

**TECHNICAL DATA:** **(Ta = 25°C )**

| Parameter name | Symbols | Unit | Specifications 3DD505 | Parameter name | Symbols | Specifications BU104 |
|---|---|---|---|---|---|---|
| Collector-Emitter Voltage | $V_{CEO}$ | V | 400 | | | 150 |
| Emitter-Base Voltage | $V_{EBO}$ | V | 6 | | | 10 |
| Max. Collector Current | $I_{CM}$ | A | 5 | | | 7 |
| Max. Collector Dissipation | $P_{CM}$ | W | 75( $T_C$=25°C) | | | 85( $T_C$=25°C) |
| Junction Temperature | $T_{jm}$ | °C | 175 | | | 175 |
| Storage Temperature | $T_{stg}$ | °C | -55~+175 | | | -55~+175 |
| Emitter-Base Laekage Current | $I_{EBO}$ | mA | - | | | Max.:10 |
| | | | - | | | $V_{EB}$=10V |
| Collector-Emitter Leakage Current | $I_{CEO}$ | mA | Max.:3.0 | Collector-Base Laekage Current | $I_{CBO}$ | Max.:0.5 |
| | | | $V_{CE}$=100V | | | $V_{CB}$=100V |
| C-Base Breakdown Voltage | $V_{(BR)CBO}$ | V | - | - | | ≥400 ($I_C$=5Ma) |
| Collector- Emitter Saturation Voltage Drop | $V_{CE(sat)}$ | V | Max.:1.2 | | | Max.:1.5 |
| | | | $I_C$=1.5A,$I_B$=0.05A | | | $I_C$=7A,$I_B$=1A |
| DC Current Gain | $h_{FE}$ | | Min.:40, Max.:120 | | | Min.:15 |
| | | | $V_{CE}$= 2V, $I_C$=5A | | | $V_{CE}$= 4V, $I_C$=7A |
| Collector-Emitter Breakdown Voltage | $V_{(BR)CEO}$ | V | ≥400 | | | ≥150 |
| | | | $I_C$=1mA | | | $I_C$=5mA |
| E-Base Breakdown Voltage | $V_{(BR)EBO}$ | V | ≥6 | | | ≥10 |
| | | | $I_E$=1mA | | | $I_E$=0.5mA |

**Outline and Dimensions:**

Contact:Jiandong Lei Tel.:+86-917-6293906 Fax:+86-917-6297928 sxqlljd@hotmail.com